

TS512, TS512A

Precision dual operational amplifier

Datasheet --production data

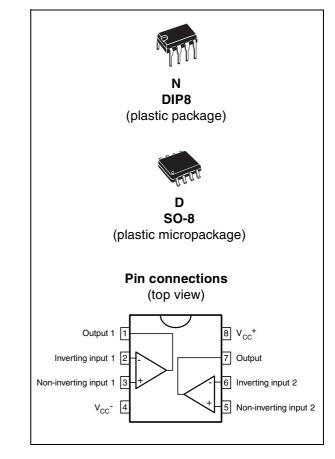
Features

- Low input offset voltage: 500 µV max. (A version)
- Low power consumption
- Short-circuit protection
- Low distortion, low noise
- High gain bandwidth product: 3 MHz
- High channel separation
- ESD protection 2 kV
- Macromodel included in this specification

Description

The TS512 device is a high-performance dual operational amplifier with frequency and phase compensation built into the chip. The internal phase compensation allows stable operation in voltage follower configurations, in spite of its high gain bandwidth product.

The circuit presents very stable electrical characteristics over the entire supply voltage range and it is particularly intended for professional and telecom applications (such as active filtering).



This is information on a product in full production.

1 Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	±18	V
V _{in}	Input voltage	±V _{CC}	
V _{id}	Differential input voltage	±(V _{CC} - 1)	
R _{thja}	Thermal resistance junction-to-ambient ⁽¹⁾ DIP8 SO-8	85 125	°C/W
R _{thjc}	Thermal resistance junction-to-case ⁽¹⁾ DIP8 SO-8	41 40	°C/W
Тj	Junction temperature	+ 150	°C
T _{stg}	Storage temperature range	-65 to +150	°C
	HBM: human body model ⁽²⁾	2	kV
ESD	MM: machine model ⁽³⁾	200	V
	CDM: charged device model ⁽⁴⁾	1.5	kV

Table 1. Absolute maximum ratings

1. Short-circuits can cause excessive heating and destructive dissipation. R_{th} are typical values.

 Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5 kΩ resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.

3. Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.

4. Charged device model: all pins and the package are charged together to the specified voltage and then discharged directly to ground through only one pin. This is done for all pins.

Table 2.Operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ⁽¹⁾	6 to 30V	V
V _{icm}	Common mode input voltage range	$V_{CC-}\text{+}1.5$ to $V_{CC+}\text{-}1.5$	V
T _{oper}	Operating free air temperature range	-40 to +125	°C

1. Value with respect to V_{CC} pin.



2 Schematic diagram

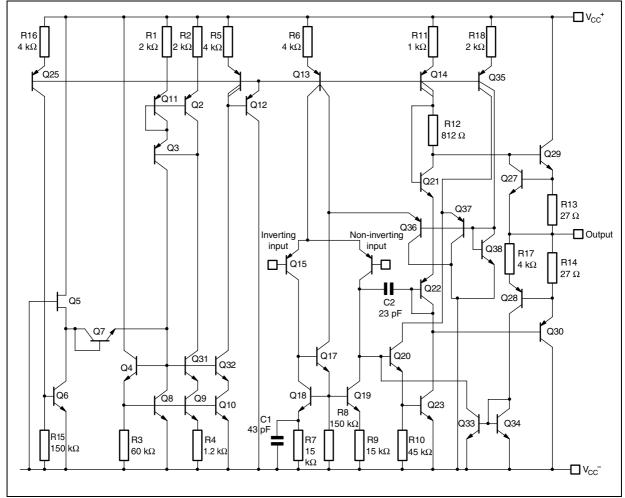


Figure 1. Schematic diagram (1/2 TS512)



3 Electrical characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
I _{CC}	Supply current (per operator) T _{min} ≤ T _{amb} ≤ T _{max}		0.5	0.6 0.75	mA
I _{ib}	Input bias current T _{min} ≤T _{amb} ≤T _{max}		50	150 300	nA
R _{in}	Input resistance, f = 1 kHz		1		MΩ
V _{io}	Input offset voltage TS512 TS512A T _{min} ≤ T _{amb} ≤ T _{max} TS512 TS512A		0.5	2.5 0.5 3.5 1.5	mV
ΔV_{io}	Input offset voltage drift T _{min} ≤ T _{amb} ≤ T _{max}		2		μV/°C
I _{io}	Input offset current T _{min} ≤ T _{amb} ≤ T _{max}		5	20 40	nA
ΔI_{io}	Input offset current drift T _{min} ≤ T _{amb} ≤ T _{max}		0.08		<u>nA</u> °C
I _{os}	Output short-circuit current		23		mA
A _{vd}	Large signal voltage gain $R_L = 2 k\Omega, V_{CC} = \pm 15 V, T_{min} \le T_{amb} \le T_{max}$ 90 $V_{CC} = \pm 4 V$		100 95		dB
GBP	Gain bandwidth product, f = 100 kHz	1.8	3		MHz
e _n	Equivalent input noise voltage, f = 1 kHz Rs = 50 Ω Rs = 1 k Ω Rs = 10 k Ω		8 10 18		<u>nV</u> √Hz
THD	Total harmonic distortion $A_v = 20 \text{ dB}, R_L = 2 \text{ k}\Omega$ $V_o = 2 \text{ V}_{pp}, f = 1 \text{ kHz}$		0.03		%
±V _{opp}	Output voltage swing $ \begin{array}{l} R_L = 2 \; k\Omega, \; V_{CC} = \pm 15 \; \text{V}, \; T_{min} \leq T_{amb} \leq T \;_{max} \\ V_{CC} = \pm 4 \; \text{V} \end{array} $	±13	±3		V
V _{opp}	Large signal voltage swing $R_L = 10 \text{ k}\Omega$, f = 10 kHz		28		V _{pp}
SR	Slew rate Unity gain, $R_L = 2 k\Omega$	0.8	1.5		V/µs
CMR	Common mode rejection ratio $CMR = 20 \log (\Delta V_{ic}/\Delta V_{io})$ $(V_{ic} = -10 V to 10 V, V_{out} = V_{CC}/2, R_L > 1 M\Omega)$	90			dB

Table 3. $V_{CC} = \pm 15 \text{ V}, \text{ T}_{amb} = 25 \text{ °C}$ (unless otherwise specified)



Symbol	Parameter	Min.	Тур.	Max.	Unit
SVR	Supply voltage rejection ratio 20 log $(\Delta V_{CC}/\Delta V_{io})$ $(V_{CC} = \pm 4$ V to ± 15 V, $V_{out} = V_{icm} = V_{CC}/2)$	90			dB
V_{o1}/V_{o2}	Channel separation, f = 1 kHz		120		dB

Table 3. $V_{CC} = \pm 15 \text{ V}, T_{amb} = 25 \text{ °C}$ (unless otherwise specified) (continued)



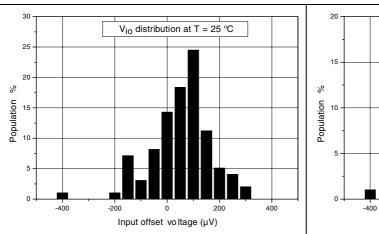
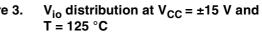
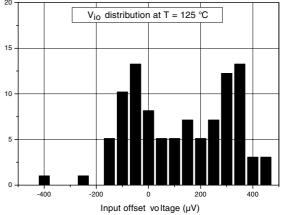
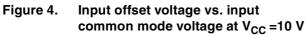
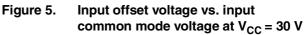


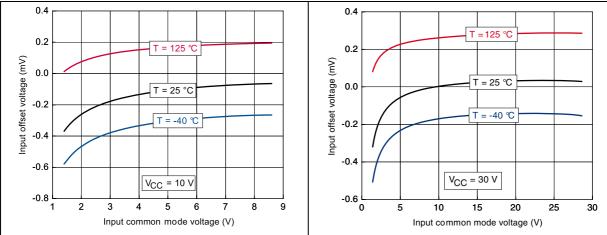
Figure 2. V_{io} distribution at $V_{CC} = \pm 15$ V and Figure 3. V_{io} distribution T = 25 °C T = 125 °C

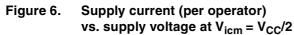


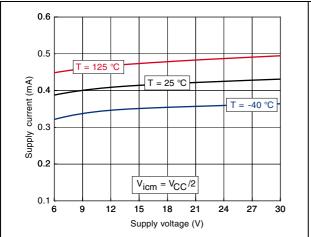


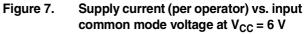


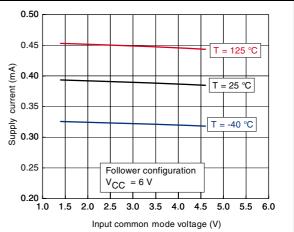














Supply current (per operator) vs. input

Figure 8. Supply current (per operator) vs. input Figure 9. common mode voltage at $V_{CC} = 10 \text{ V}$

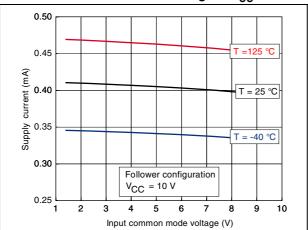


Figure 10. Output current vs. supply voltage at $V_{icm} = V_{CC}/2$

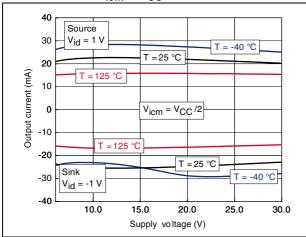
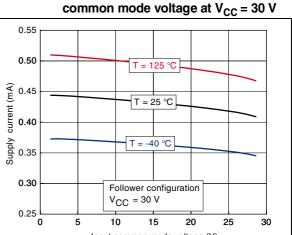
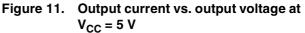


Figure 12. Output current vs. output voltage at $V_{CC} = 30 V$

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Input common mode voltage (V)



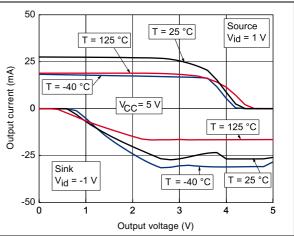


Figure 13. Voltage gain and phase for different capacitive loads at V_{CC} = 6 V, V_{icm} = 3 V and T = 25 °C

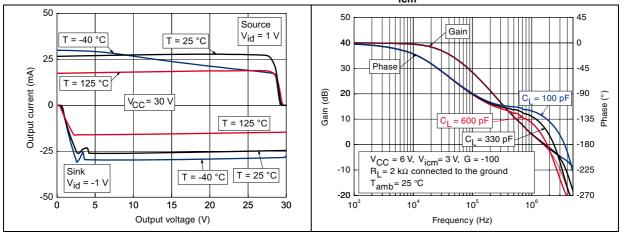




Figure 14.Voltage gain and phase for different Figure 15.
capacitive loads at $V_{CC} = 10 \text{ V}$,
 $V_{icm} = 5 \text{ V}$ and T = 25 °CVoltage gain and phase for different
capacitive loads at $V_{CC} = 30 \text{ V}$,
 $V_{icm} = 15 \text{ V}$ and T = 25 °C

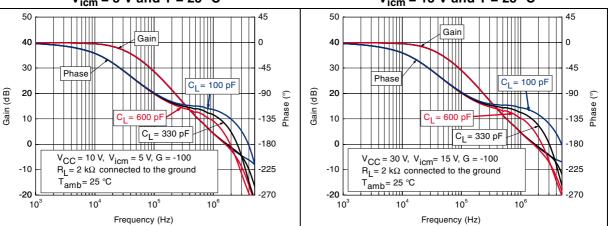
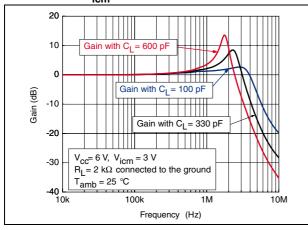
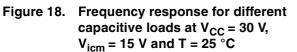
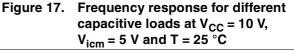


Figure 16. Frequency response for different capacitive loads at $V_{CC} = 6 V$, $V_{icm} = 3 V$ and T = 25 °C







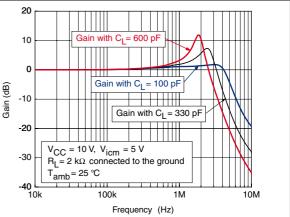


Figure 19. Phase margin vs. output current, at $V_{CC} = 6 V$, $V_{icm} = 3 V$ and T = 25 °C

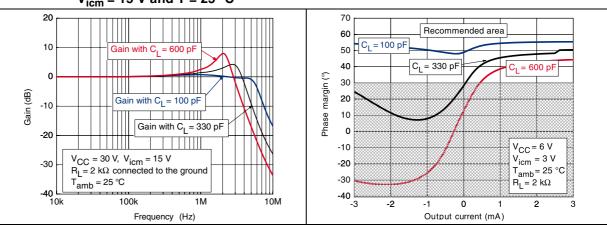
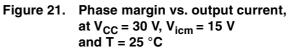
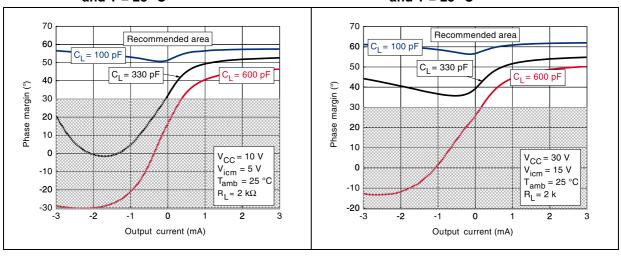


Figure 20. Phase margin vs. output current, at V_{CC} = 10 V, V_{icm} = 5 V and T = 25 °C







4 Macromodel

4.1 Important notes concerning this macromodel

- All models are a trade-off between accuracy and complexity (i.e. simulation time).
- Macromodels are not a substitute to breadboarding; rather, they confirm the validity of a design approach and help to select surrounding component values.
- A macromodel emulates the **nominal** performance of a **typical** device within **specified operating conditions** (temperature, supply voltage, for example). Thus the macromodel is often not as exhaustive as the datasheet, its purpose is to illustrate the main parameters of the product.

Data derived from macromodels used outside of the specified conditions (V_{CC} , temperature, for example) or even worse, outside of the device operating conditions (V_{CC} , V_{icm} , for example), is not reliable in any way.

4.2 Macromodel code

```
** Standard Linear Ics Macromodels, 1993.
** CONNECTIONS :
* 1 INVERTING INPUT
* 2 NON-INVERTING INPUT
* 3 OUTPUT
* 4 POSITIVE POWER SUPPLY
* 5 NEGATIVE POWER SUPPLY
.SUBCKT TS512 1 3 2 4 5
.MODEL MDTH D IS=1E-8 KF=6.565195E-17 CJO=10F
* INPUT STAGE
CIP 2 5 1.00000E-12
CIN 1 5 1.00000E-12
EIP 10 5 2 5 1
EIN 16 5 1 5 1
RIP 10 11 2.600000E+01
RIN 15 16 2.600000E+01
RIS 11 15 1.061852E+02
DIP 11 12 MDTH 400E-12
DIN 15 14 MDTH 400E-12
VOFP 12 13 DC 0
VOFN 13 14 DC 0
IPOL 13 5 1.000000E-05
CPS 11 15 12.47E-10
DINN 17 13 MDTH 400E-12
VIN 17 5 1.500000e+00
DINR 15 18 MDTH 400E-12
```



VIP 4 18 1.500000E+00 FCP 4 5 VOFP 3.400000E+01 FCN 5 4 VOFN 3.400000E+01 FIBP 2 5 VOFN 1.000000E-02 FIBN 5 1 VOFP 1.000000E-02 * AMPLIFYING STAGE FIP 5 19 VOFP 9.000000E+02 FIN 5 19 VOFN 9.000000E+02 RG1 19 5 1.727221E+06 RG2 19 4 1.727221E+06 CC 19 5 6.00000E-09 DOPM 19 22 MDTH 400E-12 DONM 21 19 MDTH 400E-12 HOPM 22 28 VOUT 6.521739E+03 VIPM 28 4 1.500000E+02 HONM 21 27 VOUT 6.521739E+03 VINM 5 27 1.500000E+02 GCOMP 5 4 4 5 6.485084E-04 RPM1 5 80 1E+06 RPM2 4 80 1E+06 GAVPH 5 82 19 80 2.59E-03 RAVPHGH 82 4 771 RAVPHGB 82 5 771 RAVPHDH 82 83 1000 RAVPHDB 82 84 1000 CAVPHH 4 83 0.331E-09 CAVPHB 5 84 0.331E-09 EOUT 26 23 82 5 1 VOUT 23 5 0 ROUT 26 3 6.498455E+01 COUT 3 5 1.00000E-12 DOP 19 25 MDTH 400E-12 VOP 4 25 1.742230E+00 DON 24 19 MDTH 400E-12 VON 24 5 1.742230E+00 .ENDS



Table 4.	$v_{CC} = \pm 15 v$, $T_{amb} = 25 C (unless otherwise specified)$					
Symbol	Conditions	Value	Unit			
V _{io}		0	mV			
A _{vd}	$R_L = 2 k\Omega$	100	V/mV			
I _{CC}	No load, per operator	350	μΑ			
V _{icm}		-13.4 to 14	V			
V _{OH}	$R_L = 2 k\Omega$	+14	V			
V _{OL}	$R_L = 2 k\Omega$	-14	V			
I _{sink}	V _o = 0 V	27.5	mA			
Isource	V _o = 0 V	27.5	mA			
GBP	$R_{L} = 2 k\Omega, C_{L} = 100 pF$	2.5	MHz			
SR	$R_L = 2 k\Omega$	1.4	V/μs			
Øm	$R_{L} = 2 k\Omega, C_{L} = 100 pF$	55	Degrees			

Table 4. $V_{CC} = \pm 15 \text{ V}, T_{amb} = 25 \text{ °C}$ (unless otherwise specified)



5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.



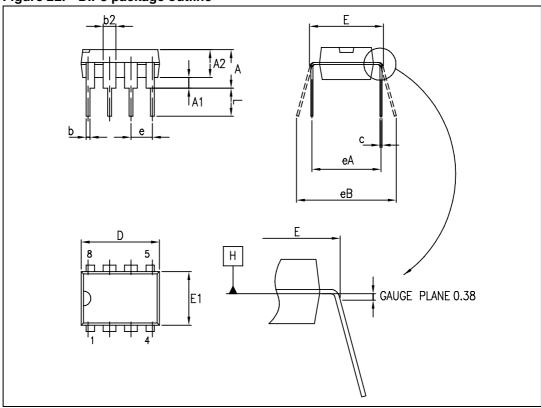


Figure 22. DIP8 package outline

	Dimensions						
Symbol		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			5.33			0.210	
A1	0.38			0.015			
A2	2.92	3.30	4.95	0.115	0.130	0.195	
b	0.36	0.46	0.56	0.014	0.018	0.022	
b2	1.14	1.52	1.78	0.045	0.060	0.070	
С	0.20	0.25	0.36	0.008	0.010	0.014	
D	9.02	9.27	10.16	0.355	0.365	0.400	
Е	7.62	7.87	8.26	0.300	0.310	0.325	
E1	6.10	6.35	7.11	0.240	0.250	0.280	
е		2.54			0.100		
eA		7.62			0.300		
eB			10.92			0.430	
L	2.92	3.30	3.81	0.115	0.130	0.150	

Table 5.DIP8 package mechanical data



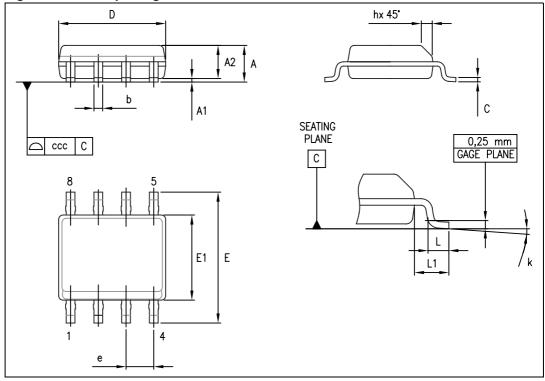


Figure 23. SO-8 package outline



Table 6.		ge mechanica	aiuala				
	Dimensions						
Symbol	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.75			0.069	
A1	0.10		0.25	0.004		0.010	
A2	1.25			0.049			
b	0.28		0.48	0.011		0.019	
С	0.17		0.23	0.007		0.010	
D	4.80	4.90	5.00	0.189	0.193	0.197	
Е	5.80	6.00	6.20	0.228	0.236	0.244	
E1	3.80	3.90	4.00	0.150	0.154	0.157	
е		1.27			0.050		
h	0.25		0.50	0.010		0.020	
L	0.40		1.27	0.016		0.050	
L1		1.04			0.040		
k	0		8°	1°		8°	
ссс			0.10			0.004	



6 Ordering information

Table 7. Order codes

Order code	Temperature range	Package	Packaging	Marking
TS512IN		DIP8	Tube	512IN
TS512AIN		DIF6	Tube	512AIN
TS512ID TS512IDT	-40 °C, + 125 °C	SO-8	Tube or	5121
TS512AID TS512AIDT			tape and reel	512AI
TS512IYDT ⁽¹⁾		SO-8 (automotive grade)	Tube or tape and reel	512IY
TS512AIYDT ⁽¹⁾		(automotive grade)	Tape and reel	512AIY

1. Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q 002 or equivalent are ongoing.



7 Revision history

Table 8.	Document revision history

Date	Revision	Changes
21-Nov-2001	1	Initial release.
23-Jun-2005	2	PPAP references inserted in the datasheet, see <i>Table 7: Order codes</i> .
05-May-2008	3	AC and DC performance characteristics curves added for V_{CC} = 6V, V_{CC} = 10V and V_{CC} = 30V. Modified I _{CC} typ, added parameters over temperature range in electrical characteristics table. Corrected macromodel information.
04-Feb-2010	4	Updated document format. Added TS512A and related parameters. Modified footnote <i>1</i> under <i>Table 2</i> . Removed <i>Figure 11</i> . Modified <i>Figure 12</i> and <i>Figure 13</i> . Removed TS512AIYD order code from <i>Table 7</i> .
12-Sep-2012	5	Updated CMR and SVR test conditions in <i>Table 3</i> . Removed TS512IYD order code from <i>Table 7</i> . Minor corrections throughout document.



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